

CLAIMS (with indication of amended or new):

1. (AMENDED) An apparatus for forming an ultra-thin film of a semiconductor device comprising:
- a reactive chamber consisting of an upper container and a lower container junctioned by an O-ring;
 - a susceptor installed inside the reactive chamber for supporting a target substrate on which an ultra-thin film is to be formed;
 - at least two gas supply pipes for supplying at least two material gases into the reactive chamber to form an ultra-thin film on the substrate;
 - at least two gas supply controllers respectively installed at the gas supply pipes to repeatedly supply the material gases alternately into the chamber;
 - a gas outlet for discharging the gas from the chamber;
 - at least two remote plasma generators installed outside the reactive chamber and respectively connected to the gas supply pipes for activating the material gases supplied through the gas supply pipes; and
 - a temperature controller for controlling the temperature inside the chamber in a heat exchange method, the temperature controller being installed to surround the chamber.